



Micro Commercial Components  
20736 Marilla Street Chatsworth  
CA 91311  
Phone: (818) 701-4933  
Fax: (818) 701-4939

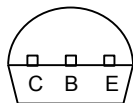
# 2N5401

## PNP Silicon Amplifier Transistor 625mW

### Features

- Through Hole Package
- 150°C Junction Temperature

Pin Configuration  
Bottom View

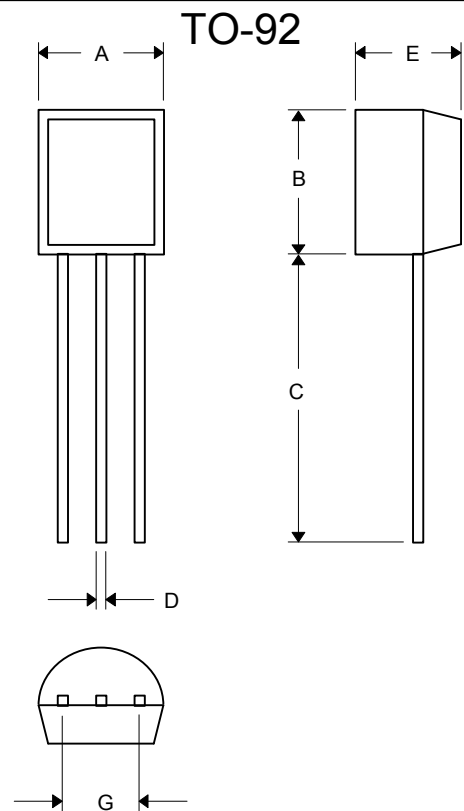


### Mechanical Data

- Case: TO-92, Molded Plastic
- Marking: 2N5401

### Maximum Ratings @ 25°C Unless Otherwise Specified

Charateristic	Symbol	Value	Unit
Collector-Emitter Voltage	$V_{CEO}$	150	V
Collector-Base Voltage	$V_{CBO}$	160	V
Emitter-Base Voltage	$V_{EBO}$	5.0	V
Collector Current(DC)	$I_C$	600	mA
Power Dissipation@ $T_A=25^\circ\text{C}$ Derate above 25°C	$P_d$	625 5.0	mW mW/°C
Power Dissipation@ $T_C=25^\circ\text{C}$ Derate above 25°C	$P_d$	1.5 12	W mW/°C
Maximum Thermal Resistance, Junction to Ambient Air	$R_{\theta JA}$	200	°C/mW
Maximum Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/mW
Operating & Storage Temperature	$T_j, T_{STG}$	-55~150	°C



DIM	DIMENSIONS				NOTE
	INCHES		MM		
	MIN	MAX	MIN	MAX	
A	.175	.185	4.45	4.70	
B	.175	.185	4.46	4.70	
C	.500	---	12.7	---	
D	.016	.020	0.41	0.63	
E	.135	.145	3.43	3.68	
G	.095	.105	2.42	2.67	

**ELECTRICAL CHARACTERISTICS** ( $T_A = 25^\circ\text{C}$  unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Collector–Emitter Breakdown Voltage <sup>(1)</sup> ( $I_C = 1.0\text{ mA}$ , $I_B = 0$ )	$V_{(BR)CEO}$	150	—	Vdc
Collector–Base Breakdown Voltage ( $I_C = 100\text{ }\mu\text{A}$ , $I_E = 0$ )	$V_{(BR)CBO}$	160	—	Vdc
Emitter–Base Breakdown Voltage ( $I_E = 10\text{ }\mu\text{A}$ , $I_C = 0$ )	$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current ( $V_{CB} = 120\text{ Vdc}$ , $I_E = 0$ ) ( $V_{CB} = 120\text{ Vdc}$ , $I_E = 0$ , $T_A = 100^\circ\text{C}$ )	$I_{CBO}$	—	50	
Emitter Cutoff Current ( $V_{EB} = 3.0\text{ Vdc}$ , $I_C = 0$ )	$I_{EBO}$	—	50	nAdc

**ON CHARACTERISTICS(1)**

DC Current Gain ( $I_C = 1.0\text{ mA}$ , $V_{CE} = 5.0\text{ Vdc}$ ) ( $I_C = 10\text{ mA}$ , $V_{CE} = 5.0\text{ Vdc}$ ) ( $I_C = 50\text{ mA}$ , $V_{CE} = 5.0\text{ Vdc}$ )	$h_{FE}$	50 60 50	— 240 —	—
Collector–Emitter Saturation Voltage ( $I_C = 10\text{ mA}$ , $I_B = 1.0\text{ mA}$ ) ( $I_C = 50\text{ mA}$ , $I_B = 5.0\text{ mA}$ )	$V_{CE(sat)}$	— —	0.2 0.5	Vdc
Base–Emitter Saturation Voltage ( $I_C = 10\text{ mA}$ , $I_B = 1.0\text{ mA}$ ) ( $I_C = 50\text{ mA}$ , $I_B = 5.0\text{ mA}$ )	$V_{BE(sat)}$	— —	1.0 1.0	Vdc

**SMALL–SIGNAL CHARACTERISTICS**

Current–Gain — Bandwidth Product ( $I_C = 10\text{ mA}$ , $V_{CE} = 10\text{ Vdc}$ , $f = 100\text{ MHz}$ )	$f_T$	100	300	MHz
Output Capacitance ( $V_{CB} = 10\text{ Vdc}$ , $I_E = 0$ , $f = 1.0\text{ MHz}$ )	$C_{obo}$	—	6.0	pF
Small–Signal Current Gain ( $I_C = 1.0\text{ mA}$ , $V_{CE} = 10\text{ Vdc}$ , $f = 1.0\text{ kHz}$ )	$h_{fe}$	40	200	—
Noise Figure ( $I_C = 250\text{ }\mu\text{A}$ , $V_{CE} = 5.0\text{ Vdc}$ , $R_S = 1.0\text{ k}\Omega$ , $f = 1.0\text{ kHz}$ )	NF	—	8.0	dB

1. Pulse Test: Pulse Width = 300  $\mu\text{s}$ , Duty Cycle = 2.0%.

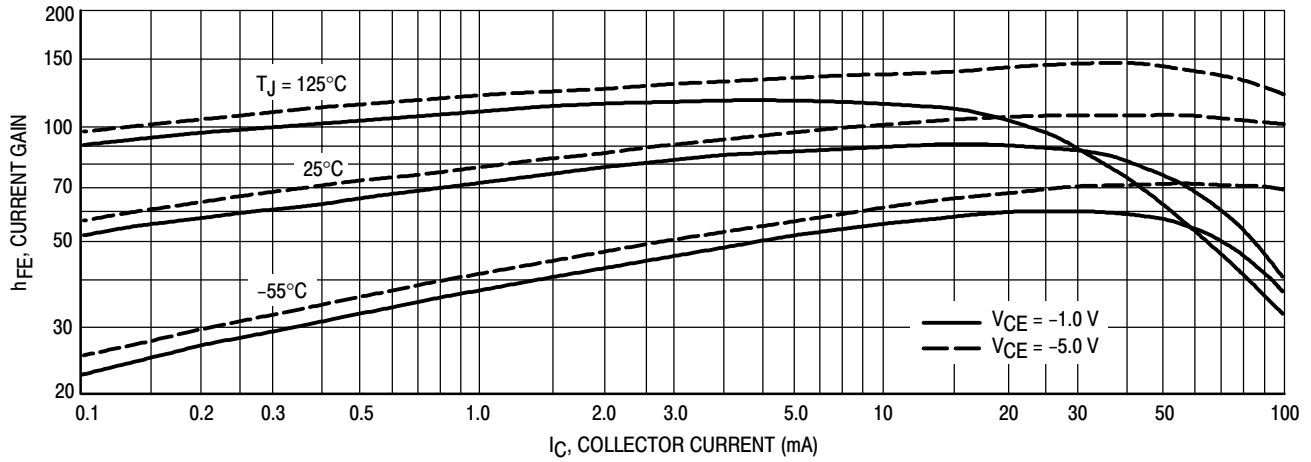


Figure 1. DC Current Gain

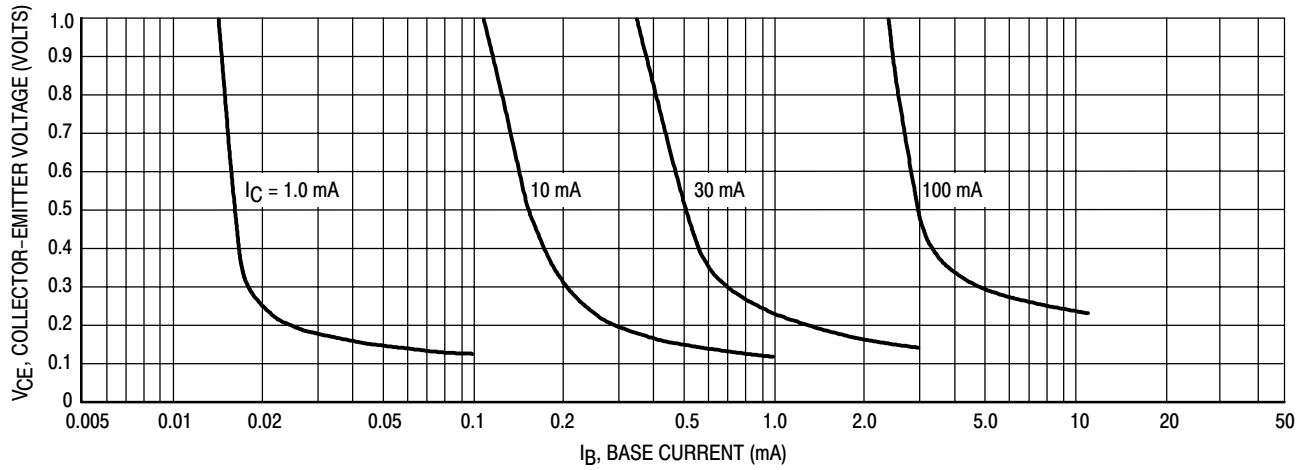


Figure 2. Collector Saturation Region

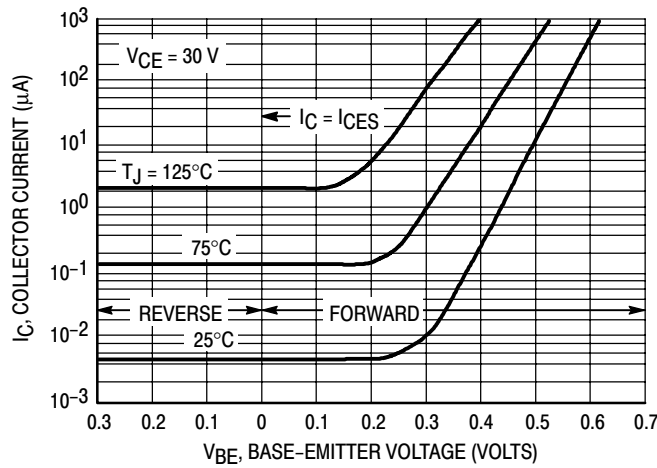


Figure 3. Collector Cut-Off Region

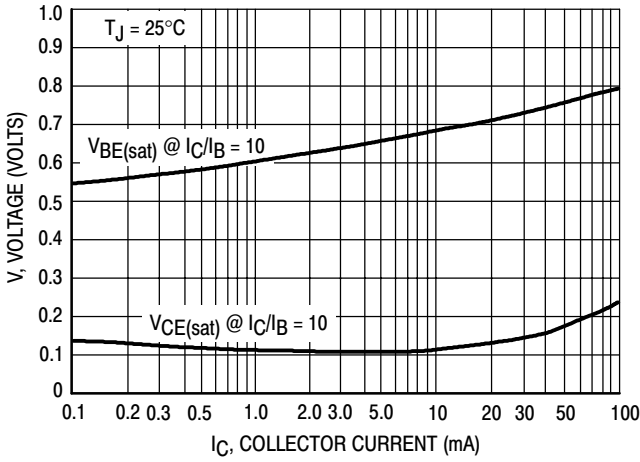


Figure 4. "On" Voltages

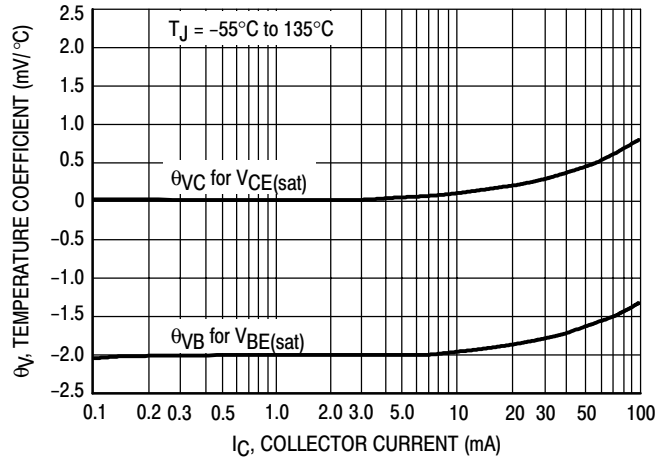


Figure 5. Temperature Coefficients

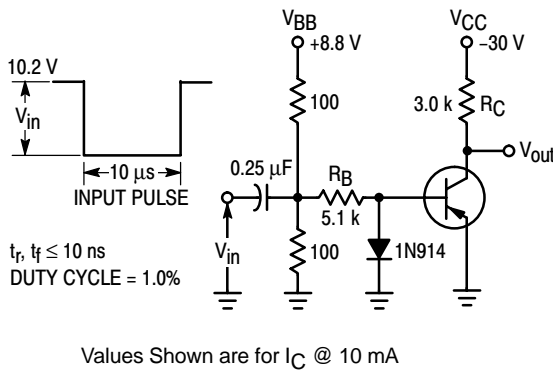


Figure 6. Switching Time Test Circuit

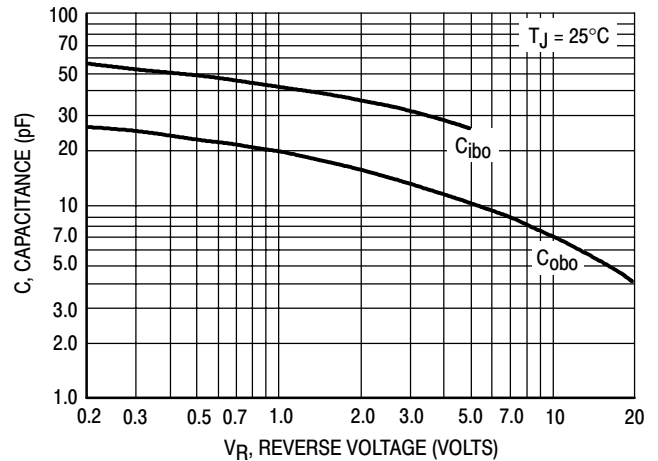


Figure 7. Capacitances

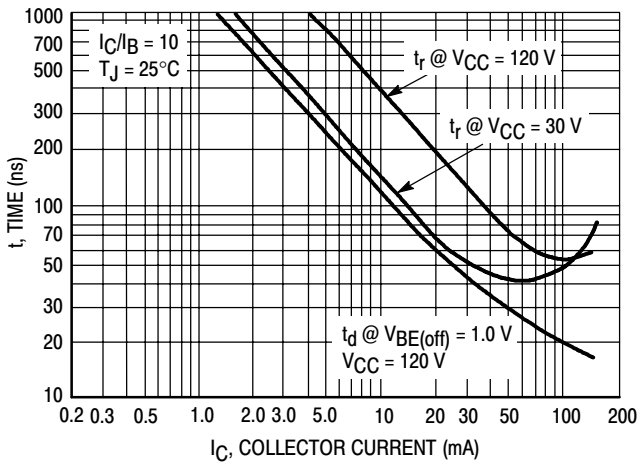


Figure 8. Turn-On Time

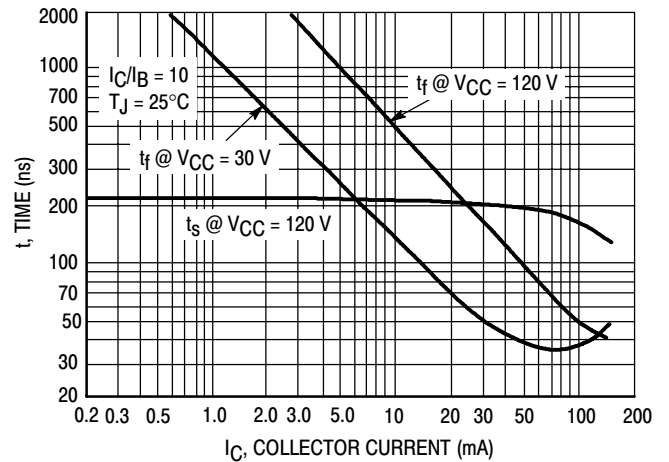


Figure 9. Turn-Off Time